**HALOGEN** 

FREE



## 1.2 A Slew Rate Controlled Load Switch

#### **DESCRIPTION**

The SiP4282 series is a slew rate controlled high side switch. The switch is of a low on resistance p-channel MOSFET that supports continuous current up to 1.2 A.

The SiP4282 series operates with an input voltage from 1.8 V to 5.5 V. It offers under voltage lock out that turns the switch off when an input under voltage condition exists. The "A" option without UVLO extends the minimum operation voltage from 1.8 V down to 1.5 V. The SiP4282 is available in two different versions of slew rates, 100 µs and 1 ms. The SiP4282 series integrates load discharge circuit to ensure the discharge of capacitive load when the switch is disabled.

The SiP4282 features low input logic level to interface with low control voltage from microprocessors. This device has a very low operating current (typically 2.5  $\mu$ A for SiP4282 and 50 pA for SiP4282A).

The SiP4282 is available in lead (Pb)-free package options including 6 pin PowerPAK® SC-75-6, and 4 pin TDFN4 1.2 mm x 1.6 mm DFN4 packages. The operation temperature range is specified from -40 °C to +85 °C.

The SiP4282 compact package options, operation voltage range, and low operating current make it a good fit for battery power applications.

#### **FEATURES**

- 1.8 V to 5.5 V input voltage range for SiP4282
- 1.5 V to 5.5 V input voltage range for SiP4282A
- Very low R<sub>DS(on)</sub>, typically 105 mW at 5 V and 175 mW at 3 V
- Slew rate controlled turn-on time options: 100 µs and 1 ms
- · Fast shutdown load discharge
- Low quiescent current, 4 μA for SiP4282
- Low quiescent current, 1 μA for SiP4282A
- Low shutdown current < 1 μA</li>
- UVLO of 1.4 V for SiP4282
- PowerPAK SC-75 1.6 mm x 1.6 mm and TDFN4 1.2 mm x 1.6 mm packages
- Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912">www.vishay.com/doc?99912</a>

#### **APPLICATIONS**

- Cellular telephones
- Digital still cameras
- Personal digital assistants (PDA)
- Hot swap supplies
- Notebook computers
- · Personal communication devices
- Portable Instruments

#### **TYPICAL APPLICATION CIRCUIT**

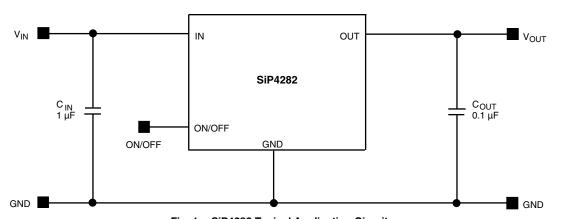


Fig. 1 - SiP4282 Typical Application Circuit

ORDERING INFORMATION									
TEMPERATURE RANGE	PACKAGE	SLEW RATE (TYP.)	UNDER VOLTAGE LOCKOUT	MARKING	PART NUMBER				
-40 °C to +85 °C	PowerPAK	100 μs	No	LExxx	SiP4282ADVP3-T1GE3				
	SC-75-6	100 μs	Yes	LFxxx	SiP4282DVP3-T1GE3				
	TDFN4 1.2 x 1.6	100 μs	No	Bx	SiP4282ADNP3-T1GE4				
		100 µs	Yes	Cx	SiP4282DNP3-T1GE4				

#### Note

xxx = lot code

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ABSOLUTE MAXIMUM RATII	IGS			
PARAMETER		LIMIT	UNIT	
Supply input voltage (V <sub>IN</sub> )		-0.3 to 6		
Enable input voltage (V <sub>ON / OFF</sub> )		-0.3 to 6		
Output voltage (V <sub>OUT</sub> )		-0.3 to V <sub>IN</sub> + 0.3		
Maximum continuous switch current (Ima	ι.)	1.4		
Marian and Invalid and Invalid	V <sub>IN</sub> ≥ 2.5 V	3	Α	
Maximum pulsed current (I <sub>DM</sub> ) V <sub>IN</sub>	V <sub>IN</sub> < 2.5 V	1.6	1	
ESD rating (HBM)	·	4000	V	
Junction temperature (T <sub>J</sub> )		-40 to +125	°C	
The amount of the control of the con	6 pin PPAK SC75 b	90	9000	
Thermal resistance (θ <sub>JA</sub> ) <sup>a</sup>	4 pin TDFN4 1.2 mm x 1.6 mm °	170	°C/W	
Device finalization (D.) 3	6 pin PPAK SC75 b	610	ma\\/	
Power fissipation (P <sub>D</sub> ) <sup>a</sup>	4 pin TDFN4 1.2 mm x 1.6 mm °	324	mW	

#### **Notes**

- Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability
- a. Device mounted with all leads and power pad soldered or welded to PC board
- b. Derate 11.1 mW/ $^{\circ}$ C above  $T_A = 70 \,^{\circ}$ C
- c. Derate 5.9 mW/ $^{\circ}$ C above  $T_A = 70$   $^{\circ}$ C, see PCB layout

RECOMMENDED OPERATING RANGE							
PARAMETER	LIMIT	UNIT					
Input voltage range (V <sub>IN</sub> ) for SiP4282 version	1.8 to 5.5	V					
Input voltage range (V <sub>IN</sub> ) for SiP4282A version	1.5 to 5.5	V					
Operating temperature range	-40 to +85	°C					

SPECIFICATIONS								
PARAMETER	SYMBOL	TEST CONDITIONS UNLESS OTHERWISE SPECIFIED	LIMITS -40 °C to +85 °C			UNIT		
	01202	$V_{IN} = 5$ , $T_A = -40$ °C to +85 °C (typical values are at $T_A = 25$ °C)	MIN. a	TYP. b	MAX. a			
Operating voltage <sup>c</sup>	V <sub>IN</sub>	For SiP4282xxx	1.8	-	5.5			
Operating voltage	VIN	For SiP4282Axxx	1.5	-	5.5	V		
Under voltage lockout	V <sub>UVLO</sub>	For SiP4282xxx, V <sub>IN</sub> falling	1	1.4	1.8			
Under voltage lockout hysteresis	V <sub>UVLO(hyh)</sub>	For SiP4282xxx	-	250	-	mV		
Quiescent current	IQ	For SiP4282xxx, on / off = active	-	2.5	4			
Quiescent current		For SiP4282Axxx, on / off = active	-	0.00005	1	μΑ		
		V <sub>IN</sub> = 5 V, I <sub>L</sub> = 500 mA, T <sub>A</sub> = 25 °C	-	105	230	mΩ		
		V <sub>IN</sub> = 4.2 V, I <sub>L</sub> = 500 mA, T <sub>A</sub> = 25 °C	-	110	250			
On-resistance	R <sub>DS(on)</sub>	V <sub>IN</sub> = 3 V, I <sub>L</sub> = 500 mA, T <sub>A</sub> = 25 °C	-	135	290			
	20(011)	V <sub>IN</sub> = 1.8 V, I <sub>L</sub> = 500 mA, T <sub>A</sub> = 25 °C	-	230	480			
		For SiP4282Axxx, $V_{IN}$ = 1.5 V, $I_L$ = 500 mA, $T_A$ = 25 °C	-	350	520			
On-resistance temp. coefficient	resistance temp. coefficient TC <sub>RDS</sub> - 2800		-	ppm/°C				
		For SiP4282Axxx, V <sub>IN</sub> ≥ 1.5 V to < 1.8 V		-	0.3			
On / off input low voltage <sup>d</sup>	$V_{IL}$	V <sub>IN</sub> ≥ 1.8 V to < 2.7 V 0.4			0.4	V		
		$V_{IN} \ge 2.7 \text{ V to} \le 5.5 \text{ V}$	-	-	0.6			

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SPECIFICATIONS								
PARAMETER	SYMBOL	TEST CONDITIONS UNLESS OTHERWISE SPECIFIED	LIMITS -40 °C to +85 °C			UNIT		
	01111202	$V_{IN} = 5$ , $T_A = -40$ °C to $+85$ °C (typical values are at $T_A = 25$ °C)	MIN. a	TYP. b	MAX. a	•		
		$V_{IN} \geq 1.5 \; V \; to < 2.7 \; V$	1.3	-	-			
On / off input high voltage <sup>d</sup>	$V_{IH}$	$V_{IN} \geq 2.7 \; V \; to < 4.2 \; V$	1.5	-	-	V		
		$V_{IN} \geq 4.2 \; V \; to \leq 5.5 \; V$	1.8	-	-			
On / off input leakage	I <sub>SINK</sub>	V <sub>On / off</sub> = 5.5 V -		-	1	μΑ		
Output pulldown resistance	$R_{PD}$	On / off = Inactive, $T_A = 25  ^{\circ}C$	-	180	250	Ω		
SiP4282xxx3 and SiP4282Axxx3 Ver	SiP4282xxx3 and SiP4282Axxx3 Versions							
Output turn-on delay time	t <sub>d(on)</sub>	$V_{IN}$ = 5 V, $R_{LOAD}$ = 10 $\Omega,T_A$ = 25 °C	-	20	40			
Output turn-on rise time	t <sub>(on)</sub>	$V_{IN}$ = 5 V, $R_{LOAD}$ = 10 $\Omega$ , $T_A$ = 25 °C	-	140	180	μs		
Output turn-off delay time	t <sub>d(off)</sub>	$V_{IN} = 5 \text{ V}, \text{ R}_{LOAD} = 10 \ \Omega, \text{ T}_{A} = 25 \ ^{\circ}\text{C}$	-	4	10			

#### **Notes**

- a. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum
- b. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing
- c. Part requires minimum start-up of  $V_{IN} \ge 2 \ V$  to ensure operation down to 1.8 V
- d. For  $V_{\text{IN}}$  outside this range consult typical on / off threshold curve

#### **PIN CONFIGURATION**

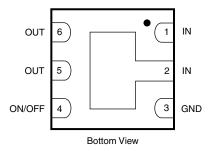


Fig. 2 - PPAK SC75-6 Package

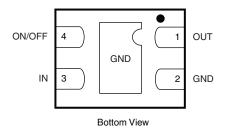


Fig. 3 - TDFN4 1.2 mm x 1.6 mm Package

PIN DESCRIPTION								
PIN NUMB	ER	NAME	FUNCTION					
PPAK	TDFN4	NAIVIE	FUNCTION					
1, 2	3	IN	This pin is the p-channel MOSFET source connection. Bypass to ground through a 1 µF capacitor					
3	2	GND	Ground connection					
4	4	ON/OFF	Enable input					
5, 6	1	OUT	This pin is the p-channel MOSFET drain connection. Bypass to ground through a 0.1 µF capacitor					



### TYPICAL CHARACTERISTICS (internally regulated, 25 °C, unless otherwise noted)

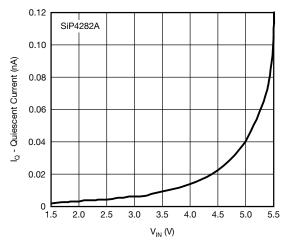


Fig. 4 - Quiescent Current vs. Input Voltage

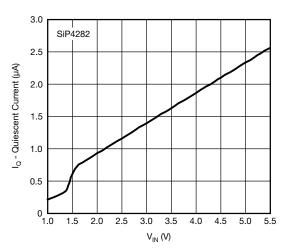


Fig. 5 - Quiescent Current vs. Input Voltage

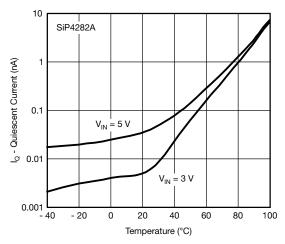


Fig. 6 - Quiescent Current vs. Temperature

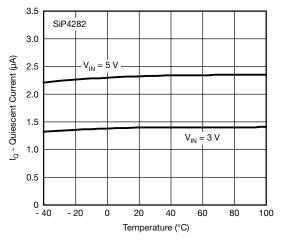


Fig. 7 - Quiescent Current vs. Temperature

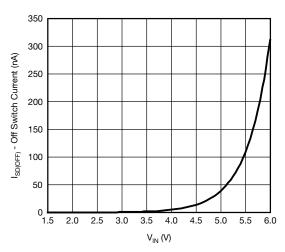


Fig. 8 - Off Switch Current vs. Input Voltage

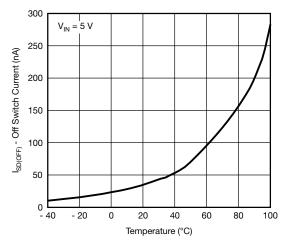


Fig. 9 - Off Switch Current vs. Temperature



### TYPICAL CHARACTERISTICS (internally regulated, 25 °C, unless otherwise noted)

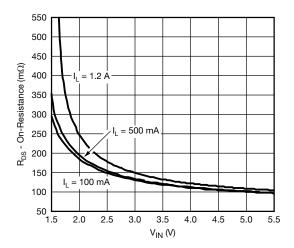


Fig. 10 - R<sub>DS(on)</sub> vs. Input Voltage

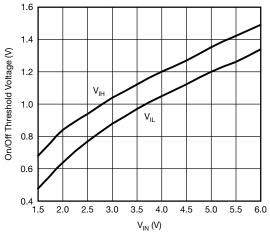


Fig. 13 - On / Off Threshold vs. Input Voltage

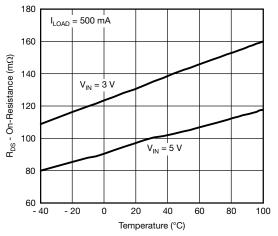


Fig. 11 - R<sub>DS(on)</sub> vs. Temperature

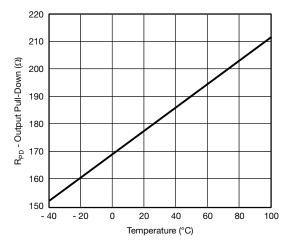
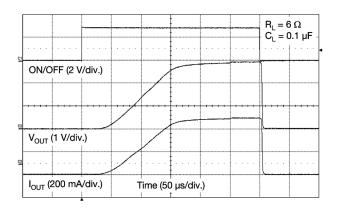


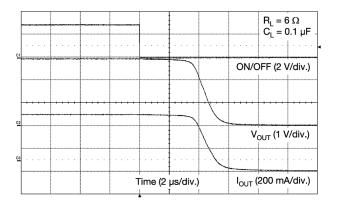
Fig. 12 - Output Pull-Down Resistance vs. Temperature



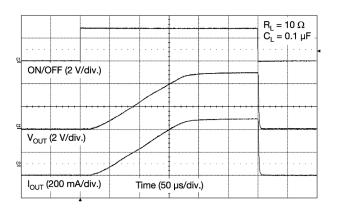
#### **TYPICAL WAVEFORMS**



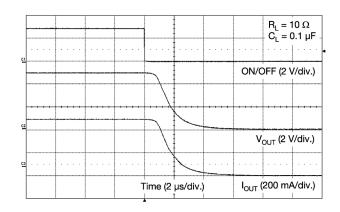
SiP4282xxx3 and SiP4282Axxx3 Switching  $(V_{IN} = 3 V)$ 



SiP4282xxx3 and SiP4282Axxx3 Turn-Off  $(V_{IN} = 3 V)$ 



SiP4282xxx3 and SiP4282Axxx3 Switching  $(V_{IN} = 5 V)$ 



SiP4282xxx3 and SiP4282Axxx3 Turn-Off  $(V_{IN} = 5 V)$ 

### **BLOCK DIAGRAM**

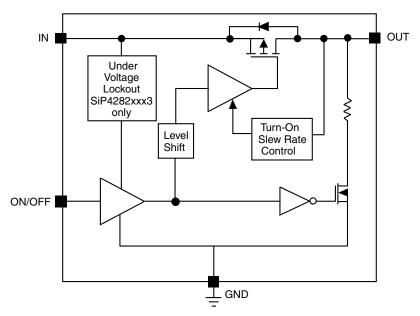


Fig. 14 - SiP4282 Functional Block Diagram

#### **PCB LAYOUT**

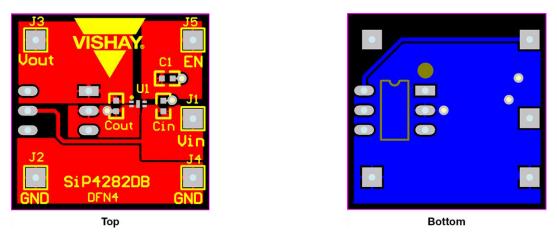


Fig. 15 - TDFN4 1.2 mm x 1.6 mm PCB Layout

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#### **DETAILED DESCRIPTION**

The SiP4282 is a p-channel MOSFET power switches designed for high-side slew rate controlled load-switching applications. Once turned on, the slew-rate control circuitry is activated and current is ramped in a linear fashion until it reaches the level required for the output load condition. This is accomplished by first elevating the gate voltage of the MOSFET up to its threshold voltage and then by linearly increasing the gate voltage until the MOSFET becomes fully enhanced. At this point, the gate voltage is then quickly increased to the full input voltage to reduce R<sub>DS(on)</sub> of the MOSFET switch and minimize any associated power losses.

All versions features a shutdown output discharge circuit which is activated at shutdown (when the part is disabled through the on / off pin) and discharges the output pin through a small internal resistor hence, turning off the load. For SiP4282-3, in instances where the input voltage falls below 1.4 V (typically) the under voltage lock-out circuitry protects the MOSFET switch from entering the saturation region or operation by shutting down the chip.

#### **APPLICATION INFORMATION**

#### **Input Capacitor**

While a bypass capacitor on the input is not required, a 1  $\mu$ F or larger capacitor for  $C_{IN}$  is recommended in almost all applications. The bypass capacitor should be placed as physically close as possible to the SiP4282 to be effective in minimizing transients on the input. Ceramic capacitors are recommended over tantalum because of their ability to withstand input current surges from low impedance sources such as batteries in portable devices.

#### **Output Capacitor**

A 0.1  $\mu$ F capacitor or larger across  $V_{OUT}$  and GND is recommended to insure proper slew operation.  $C_{OUT}$  may be increased without limit to accommodate any load transient condition with only minimal affect on the SiP4282 turn on slew rate time. There are no ESR or capacitor type requirement.

#### Enable

The on / off pin is compatible with both TTL and CMOS logic voltage levels.

#### **Protection Against Reverse Voltage Condition**

The p-channel MOSFET pass transistor has an intrinsic diode that is reversed biased when the input voltage is greater than the output voltage. Should  $V_{OUT}$  exceed  $V_{IN}$ , this intrinsic diode will become forward biased and allow excessive current to flow into the IC thru the  $V_{OUT}$  pin and potentially damage the IC device. Therefore extreme care should be taken to prevent  $V_{OUT}$  from exceeding  $V_{IN}$ .

In conditions where  $V_{OUT}$  exceeds  $V_{IN}$  a Schottky diode in parallel with the internal intrinsic diode is recommended to protect the SiP4282.

#### **Thermal Considerations**

The SiP4282 is designed to maintain a constant output load current. Due to physical limitations of the layout and assembly of the device the maximum switch current is 1.2 A, as stated in the Absolute Maximum Ratings table. However, another limiting characteristic for the safe operating load current is the thermal power dissipation of the package. To obtain the highest power dissipation (and a thermal resistance of 90 °C/W) the power pad of the device should be connected to a heat sink on the printed circuit board.

The maximum power dissipation in any application is dependent on the maximum junction temperature,  $T_J$  (max.) = 125 °C, the junction-to-ambient thermal resistance for the SC-75 PPAK package,  $\theta_{J-A}=90$  °C/W, and the ambient temperature,  $T_A$ , which may be formulaically expressed as:

$$P \text{ (max.)} = \frac{T_J \text{ (max.)} - T_A}{\theta_{J-A}} = \frac{125 - T_A}{90}$$

It then follows that, assuming an ambient temperature of 70  $^{\circ}$ C, the maximum power dissipation will be limited to about 610 mW.

So long as the load current is below the 1.2 A limit, the maximum continuous switch current becomes a function two things: the package power dissipation and the  $R_{DS(on)}$  at the ambient temperature.

As an example let us calculate the worst case maximum load current at  $T_A=70~^{\circ}\text{C}$ . The worst case  $R_{DS(on)}$  at 25  $^{\circ}\text{C}$  occurs at an input voltage of 1.8 V and is equal to 480 m $\Omega$ . The  $R_{DS(on)}$  at 70  $^{\circ}\text{C}$  can be extrapolated from this data using the following formula

 $R_{DS(on)}$  (at 70 °C) =  $R_{DS(on)}$  (at 25 °C) x (1 +  $T_C$  x  $\Delta T$ )

Where  $T_C$  is 3300 ppm/°C. Continuing with the calculation we have

 $R_{DS(on)}$  (at 70 °C) = 480 m $\Omega$  x (1 + 0.0033 x (70 °C - 25 °C)) = 551 m $\Omega$ 

The maximum current limit is then determined by

$$I_{LOAD}$$
 (max.)  $< \sqrt{\frac{P \text{ (max.)}}{R_{DS(on)}}}$ 

which in case is 1.05 A. Under the stated input voltage condition, if the 1.05 A current limit is exceeded the internal die temperature will rise and eventually, possibly damage the device.



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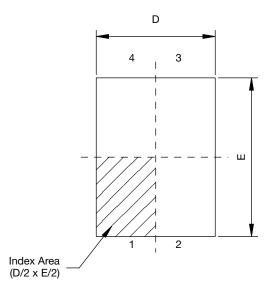
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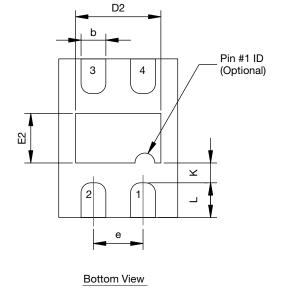
PRODUCT SUMMARY								
Part number	SiP4282	SiP4282	SiP4282A	SiP4282A				
Description	1.8 V to 5.5 V, 105 mΩ, 100 $\mu$ s rise time, with UVLO	1.8 V to 5.5 V, 105 mΩ, 100 $\mu$ s rise time, with UVLO	1.5 V to 5.5 V, 105 mΩ, 100 μs rise time	1.5 V to 5.5 V, 105 mΩ, 100 μs rise time				
Configuration	Single	Single	Single	Single				
Slew rate time (µs)	140	140	140	140				
On delay time (µs)	20	20	20	20				
Input voltage min. (V)	1.8	1.8	1.5	1.5				
Input voltage max. (V)	5.5	5.5	5.5	5.5				
On-resistance at input voltage min. (m $\Omega$ )	230	230	350	350				
On-resistance at input voltage max. (m $\Omega$ )	105	105	105	105				
Quiescent current at input voltage min. (µA)	1	1 0.00001		0.00001				
Quiescent current at input voltage max. (μA)	2.5	2.5	0.00005	0.00005				
Output discharge (yes / no)	Yes	Yes	Yes	Yes				
Reverse blocking (yes / no)	No	No	No	No				
Continuous current (A)	1.2	1.2	1.2	1.2				
Package type	TDFN4	PowerPAK SC-75-6	TDFN4	PowerPAK SC-75-6				
Package size (W, L, H) (mm)	1.2 x 1.6 x 0.5	0.75 x 1.6 x 0.5	1.2 x 1.6 x 0.5	0.75 x 1.6 x 0.5				
Status code	2	2	2	2				
Product type	Slew rate	Slew rate	Slew rate	Slew rate				
Applications	Computers, consumer, industrial, healthcare, networking, portable	Computers, consumer, industrial, healthcare, networking, portable	Computers, consumer, industrial, healthcare, networking, portable	Computers, consumer, industrial, healthcare, networking, portable				

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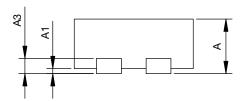


# TDFN4 1.2 x 1.6 Case Outline





Top View



Side View

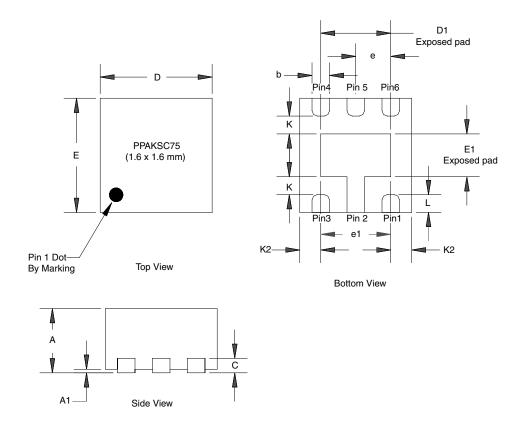
DIM.		MILLIMETERS		INCHES			
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
Α	0.45	0.55	0.60	0.017	0.022	0.024	
A1	0.00	-	0.05	0.00	-	0.002	
A3	0.	15 REF. or 0.127 REF	. (1)		0.006 or 0.005 <sup>(1)</sup>		
b	0.20	0.25	0.30	0.008	0.010	0.012	
D	1.15	1.20	1.25	0.045	0.047	0.049	
D2	0.81	0.86	0.91	0.032	0.034	0.036	
е	0.50 BSC			0.020			
Е	1.55	1.60	1.65	0.061	0.063	0.065	
E2	0.45	0.50	0.55	0.018	0.020	0.022	
K		0.25 typ.			0.010 typ.		
L	0.25	0.30	0.35	0.010	0.012	0.014	

#### Note

<sup>(1)</sup> The dimension depends on the leadframe that assembly house used.



## PowerPAK® SC75-6L (Power IC only)



		MILLIMETERS	3	INCHES			
DIM	Min	Nom	Max	Min	Nom	Max	
А	0.70	0.75	0.80	0.028	0.030	0.032	
A1	0	-	0.05	0	-	0.002	
b	0.20	0.25	0.30	0.008	0.010	0.012	
С	0.15	0.20	0.25	0.006	0.008	0.010	
D	1.55	1.60	1.65	0.0061	0.063	0.065	
D1	0.95	1.00	1.05	0.037	0.039	0.041	
E	1.55	1.60	1.65	0.061	0.063	0.065	
E1	0.55	0.60	0.65	0.022	0.024	0.026	
е		0.50 BSC			0.020 BSC		
e1	1.00 BSC			0.039 BSC			
K	0.15	-	-	0.006	-	-	
K2	0.20	-	-	0.008			
L	0.20	0.25	0.30	0.008	0.010	0.012	

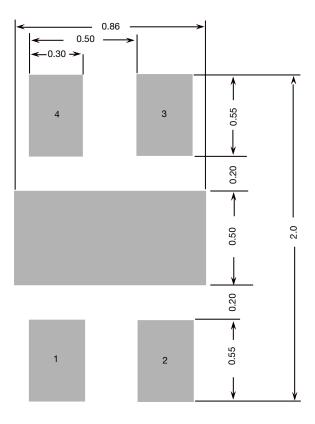
ECN: S-60845-Rev. B, 22-May-06

DWG: 5953



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### **RECOMMENDED MINIMUM PADS FOR TDFN4 1.2 x 1.6**



Recommended Minimum Pads Dimensions in mm



## **Legal Disclaimer Notice**

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